Abstracts

Fully Integrated Nonlinear Modeling and Characterization System of Microwave Transistors with On-Wafer Pulsed Measurements

J.P. Teyssier, J.P. Viaud, J.J. Raoux and R. Quere. "Fully Integrated Nonlinear Modeling and Characterization System of Microwave Transistors with On-Wafer Pulsed Measurements." 1995 MTT-S International Microwave Symposium Digest 95.3 (1995 Vol. III [MWSYM]): 1033-1036.

A novel approach for nonlinear characterization and modeling of microwave transistors has been developed. The whole process is organised as a set of methods contained in the transistor database. This implies that characterization and modeling are performed in an integrated manner. I(V) and S-parameters are measured on wafer under pulsed conditions, suitable for MESFETs, HEMTs or HBTs as illustrated by the proposed models.

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